

L Number	Hits	Search Text	DB	Time stamp
1	62	(((((shallow adj trench adj isolation) or STI)) and (photo\$1resist or resist)) and ((hydrogen or H?sub.2) same (anneal or annealling or thermal\$3 or treat\$3))) and (etch or etching)) and (polish or polishing or cmp or planarizie or (etch\$3 adj back))) and (epitaxial or epitaxy) ((shallow adj trench adj isolation) or STI)	USPAT	2003/09/26 09:25
-	5896	((shallow adj trench adj isolation) or STI)) and (photo\$1resist or resist)	USPAT	2003/09/25 14:02
-	3069	((shallow adj trench adj isolation) or STI)) and (photo\$1resist or resist) (((shallow adj trench adj isolation) or STI)) and (photo\$1resist or resist)) and (hydrogen or H?sub.2)	USPAT	2003/09/25 14:03
-	799	(((((shallow adj trench adj isolation) or STI)) and (photo\$1resist or resist)) and (hydrogen or H?sub.2)) and (((shallow adj trench adj isolation) or STI)) and (photo\$1resist or resist)) and (hydrogen or H?sub.2)	USPAT	2003/09/25 14:06
-	655	(((((shallow adj trench adj isolation) or STI)) and (photo\$1resist or resist)) and (hydrogen or H?sub.2)) and ((silicon adj nitride) or SiN or "Si.sub.3 N.sub.4")	USPAT	2003/09/25 14:05
-	304	(((((shallow adj trench adj isolation) or STI)) and (photo\$1resist or resist)) and (hydrogen or H?sub.2) same (anneal or annealling or thermal\$3 or treat\$3))	USPAT	2003/09/25 14:06
-	295	(((((shallow adj trench adj isolation) or STI)) and (photo\$1resist or resist)) and (hydrogen or H?sub.2) same (anneal or annealling or thermal\$3 or treat\$3))) and (etch or etching)	USPAT	2003/09/25 14:07
-	221	(((((shallow adj trench adj isolation) or STI)) and (photo\$1resist or resist)) and (hydrogen or H?sub.2) same (anneal or annealling or thermal\$3 or treat\$3))) and (etch or etching)) and (polish or polishing or cmp or planarizie or (etch\$3 adj back))	USPAT	2003/09/25 16:26
-	144	(((((shallow adj trench adj isolation) or STI)) and (photo\$1resist or resist)) and (hydrogen or H?sub.2) same (anneal or annealling or thermal\$3 or treat\$3))) and (etch or etching)) and (polish or polishing or cmp or planarizie or (etch\$3 adj back))) and ((trench or isolation or sti).ab. or (trench or isolation or sti).clm.)	USPAT	2003/09/25 14:10
-	19	("4582565"   "4666556"   "4671970"   "5087586"   "5244827"   "5246537"   "5248625"   "5385861"   "5387538"   "5455194"   "5472903"   "5854120"   "5895253"   "5915191"   "5926717"   "5989977"   "6001705"   "6022789"   "6358785").PN.	USPAT	2003/09/25 14:13
-	26	("3990927"   "4474975"   "5156881"   "5182221"   "5410176"   "5470798"   "5719085"   "5741740"   "5776557"   "5786039"   "5801083"   "5863827"   "5883006"   "5888880"   "5895253"   "5904540"   "5930645"   "5943585"   "5950094"   "5960299"   "5972773"   "5998280"   "6030881"   "6051447"   "6156674"   "6300219").PN.	USPAT	2003/09/25 14:18
-	62	(((((shallow adj trench adj isolation) or STI)) and (photo\$1resist or resist)) and (hydrogen or H?sub.2) same (anneal or annealling or thermal\$3 or treat\$3))) and (etch or etching)) and (polish or polishing or cmp or planarizie or (etch\$3 adj back))) and (epitaxial or epitaxy)	USPAT	2003/09/26 09:24